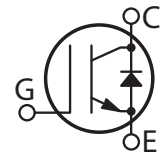


**Thunderbolt IGBT®**

The Thunderbolt IGBT® is a new generation of high voltage power IGBTs. Using Non-Punch Through Technology, the Thunderbolt IGBT® offers superior ruggedness and ultrafast switching speed.

- Low Forward Voltage Drop
- High Freq. Switching to 20KHz
- Low Tail Current
- Ultra Low Leakage Current
- RBSOA and SCSOA Rated



**MAXIMUM RATINGS**

 All Ratings:  $T_C = 25^\circ\text{C}$  unless otherwise specified.

Symbol	Parameter	APT75GT120JRDQ3	UNIT
$V_{CES}$	Collector-Emitter Voltage	1200	Volts
$V_{GE}$	Gate-Emitter Voltage	$\pm 30$	
$I_{C1}$	Continuous Collector Current @ $T_C = 25^\circ\text{C}$	97	Amps
$I_{C2}$	Continuous Collector Current @ $T_C = 110^\circ\text{C}$	42	
$I_{CM}$	Pulsed Collector Current <sup>1</sup> @ $T_C = 150^\circ\text{C}$	225	
SSOA	Switching Safe Operating Area @ $T_j = 150^\circ\text{C}$	225	
$P_D$	Total Power Dissipation	480	Watts
$T_j, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to 150	$^\circ\text{C}$
$T_L$	Max. Lead Temp. for Soldering: 0.063" from Case for 10 Sec.	300	

**STATIC ELECTRICAL CHARACTERISTICS**

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	Units
$V_{(BR)CES}$	Collector-Emitter Breakdown Voltage ( $V_{GE} = 0V, I_C = 4mA$ )	1200			Volts
$V_{GE(TH)}$	Gate Threshold Voltage ( $V_{CE} = V_{GE}, I_C = 3mA, T_j = 25^\circ\text{C}$ )	4.5	5.5	6.5	
$V_{CE(ON)}$	Collector-Emitter On Voltage ( $V_{GE} = 15V, I_C = 75A, T_j = 25^\circ\text{C}$ )	2.7	3.2	3.7	
	Collector-Emitter On Voltage ( $V_{GE} = 15V, I_C = 75A, T_j = 125^\circ\text{C}$ )		3.9		
$I_{CES}$	Collector Cut-off Current ( $V_{CE} = 1200V, V_{GE} = 0V, T_j = 25^\circ\text{C}$ ) <sup>2</sup>			200	$\mu\text{A}$
	Collector Cut-off Current ( $V_{CE} = 1200V, V_{GE} = 0V, T_j = 125^\circ\text{C}$ ) <sup>2</sup>			2000	
$I_{GES}$	Gate-Emitter Leakage Current ( $V_{GE} = \pm 20V$ )			480	nA
$R_{G(int)}$	Integrated Gate Resistor		5		$\Omega$

 CAUTION: These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

DYNAMIC CHARACTERISTICS

APT75GT120JRDQ3

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT	
$C_{ies}$	Input Capacitance	Capacitance $V_{GE} = 0V, V_{CE} = 25V$ $f = 1\text{ MHz}$		5100		pF	
$C_{oes}$	Output Capacitance			720			
$C_{res}$	Reverse Transfer Capacitance			380			
$V_{GEP}$	Gate-to-Emitter Plateau Voltage	Gate Charge $V_{GE} = 15V$ $V_{CE} = 600V$ $I_C = 75A$		10		V	
$Q_g$	Total Gate Charge <sup>3</sup>			500			
$Q_{ge}$	Gate-Emitter Charge			32			
$Q_{gc}$	Gate-Collector ("Miller") Charge			516			
SSOA	Switching Safe Operating Area	$T_J = 150^\circ C, R_G = 4.3\Omega, V_{GE} = 15V, L = 100\mu H, V_{CE} = 1200V$	225			A	
$t_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) $V_{CC} = 800V$ $V_{GE} = 15V$ $I_C = 75A$ $R_G = 1.0\Omega$ $T_J = +25^\circ C$		50		ns	
$t_r$	Current Rise Time			65			
$t_{d(off)}$	Turn-off Delay Time			375			
$t_f$	Current Fall Time			25			
$E_{on1}$	Turn-on Switching Energy <sup>4</sup>				8045		$\mu J$
$E_{on2}$	Turn-on Switching Energy (Diode) <sup>5</sup>				8845		
$E_{off}$	Turn-off Switching Energy <sup>6</sup>				2970		
$t_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C) $V_{CC} = 800V$ $V_{GE} = 15V$ $I_C = 75A$ $R_G = 1.0\Omega$ $T_J = +125^\circ C$		50		ns	
$t_r$	Current Rise Time			65			
$t_{d(off)}$	Turn-off Delay Time			415			
$t_f$	Current Fall Time			29			
$E_{on1}$	Turn-on Switching Energy <sup>4</sup>				8050		$\mu J$
$E_{on2}$	Turn-on Switching Energy (Diode) <sup>5</sup>				12660		
$E_{off}$	Turn-off Switching Energy <sup>6</sup>				4215		

THERMAL AND MECHANICAL CHARACTERISTICS

Symbol	Characteristic	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to Case (IGBT)			.26	$^\circ C/W$
$R_{\theta JC}$	Junction to Case (DIODE)			.56	
$W_T$	Package Weight		29.2		gm
$V_{Isolation}$	RMS Voltage (50-60Hz Sinusoidal Waveform From Terminals to Mounting Base for 1 Min.)	2500			Volts

- ① Repetitive Rating: Pulse width limited by maximum junction temperature.
- ② For Combi devices,  $I_{ces}$  includes both IGBT and FRED leakages
- ③ See MIL-STD-750 Method 3471.
- ④  $E_{on1}$  is the clamped inductive turn-on energy of the IGBT only, without the effect of a commutating diode reverse recovery current adding to the IGBT turn-on loss. Tested in inductive switching test circuit shown in figure 21, but with a Silicon Carbide diode.
- ⑤  $E_{on2}$  is the clamped inductive turn-on energy that includes a commutating diode reverse recovery current in the IGBT turn-on switching loss. (See Figures 21, 22.)
- ⑥  $E_{off}$  is the clamped inductive turn-off energy measured in accordance with JEDEC standard JESD24-1. (See Figures 21, 23.)

Microsemi Reserves the right to change, without notice, the specifications and information contained herein.

TYPICAL PERFORMANCE CURVES

APT75GT120JRDQ3

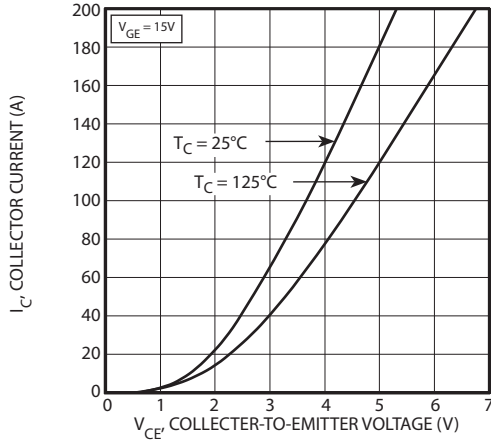


FIGURE 1, Output Characteristics ( $V_{GE} = 15V$ )

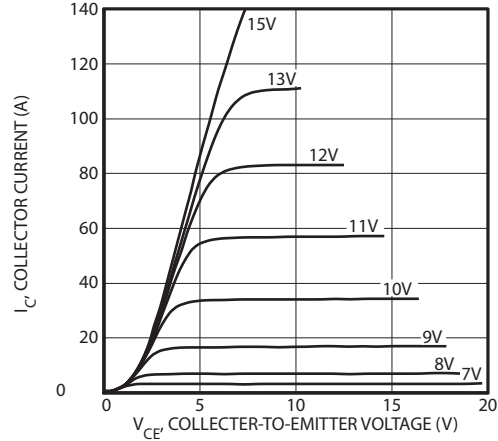


FIGURE 2, Output Characteristics ( $T_J = 125^\circ C$ )

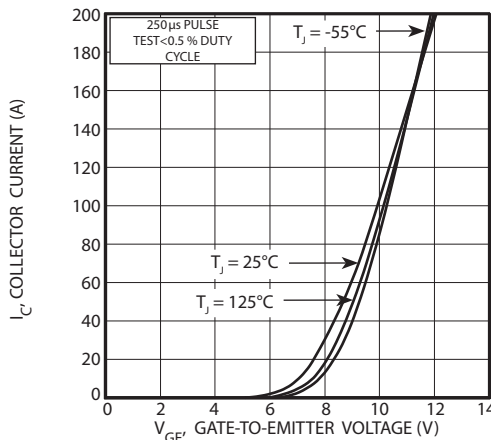


FIGURE 3, Transfer Characteristics

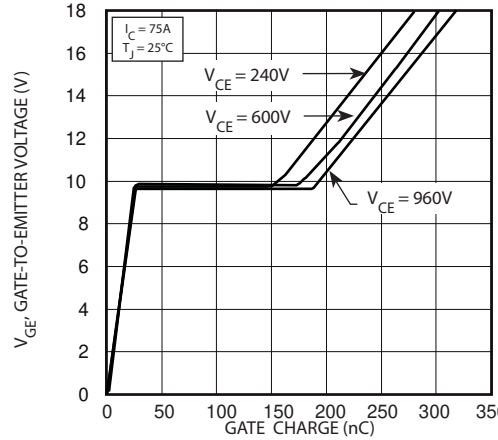


FIGURE 4, Gate Charge

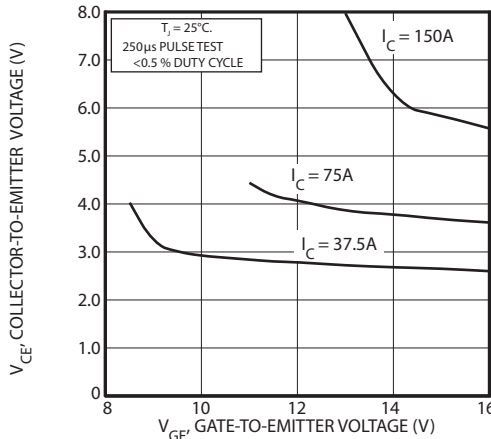


FIGURE 5, On State Voltage vs Gate-to-Emitter Voltage

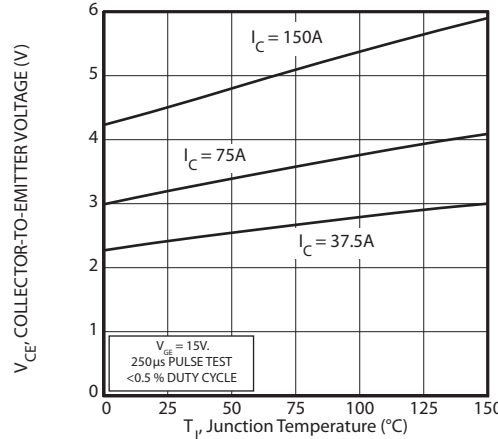


FIGURE 6, On State Voltage vs Junction Temperature

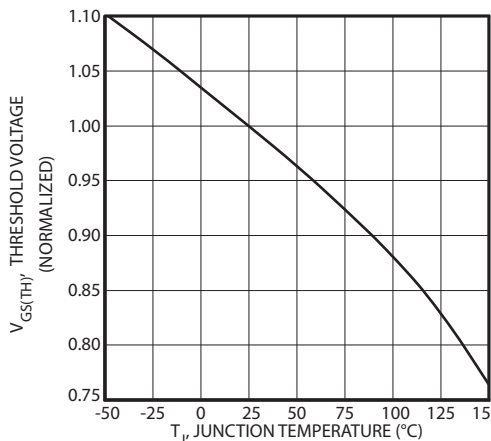


FIGURE 7, Threshold Voltage vs. Junction Temperature

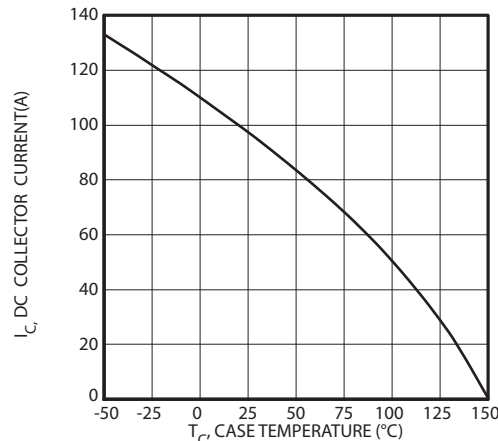


FIGURE 8, DC Collector Current vs Case Temperature

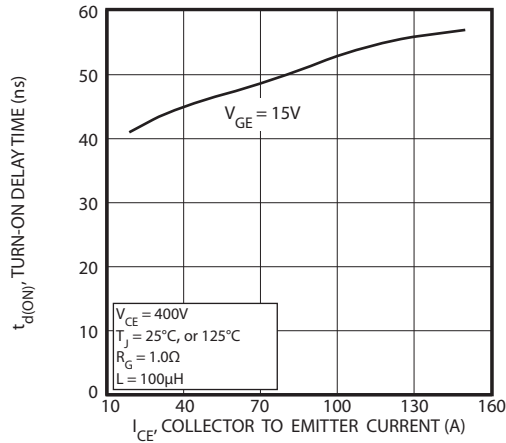


FIGURE 9, Turn-On Delay Time vs Collector Current

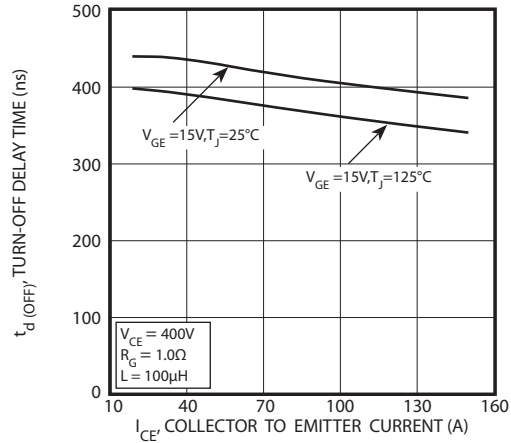


FIGURE 10, Turn-Off Delay Time vs Collector Current

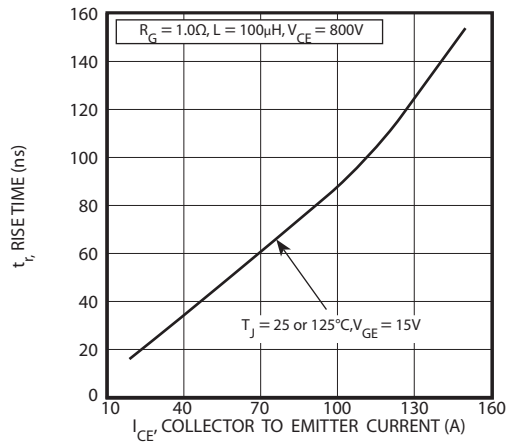


FIGURE 11, Current Rise Time vs Collector Current

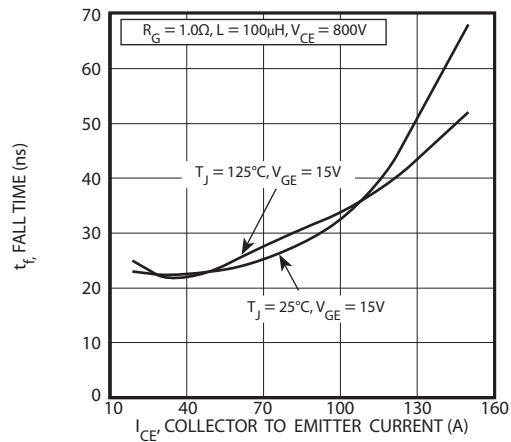


FIGURE 12, Current Fall Time vs Collector Current

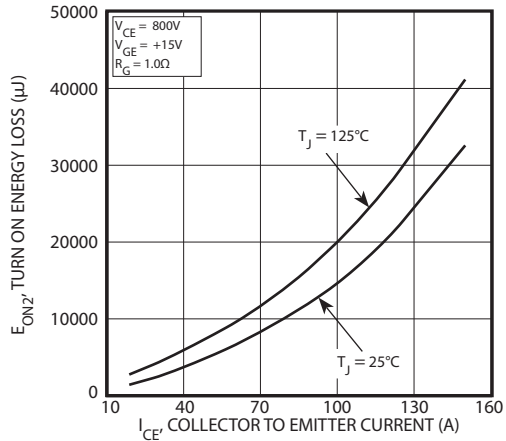


FIGURE 13, Turn-On Energy Loss vs Collector Current

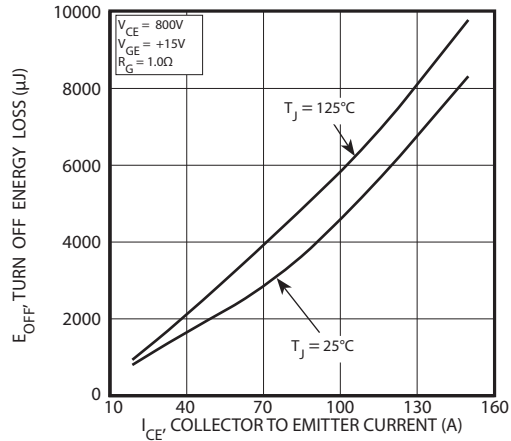


FIGURE 14, Turn Off Energy Loss vs Collector Current

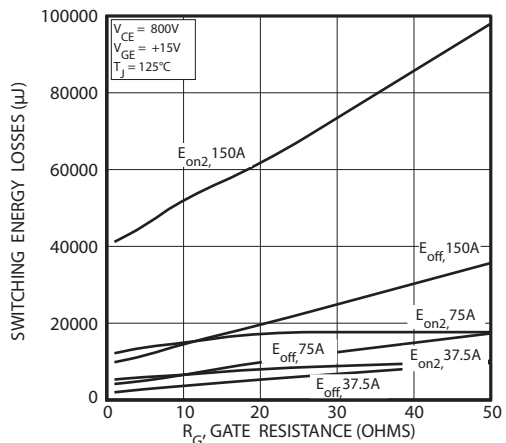


FIGURE 15, Switching Energy Losses vs. Gate Resistance

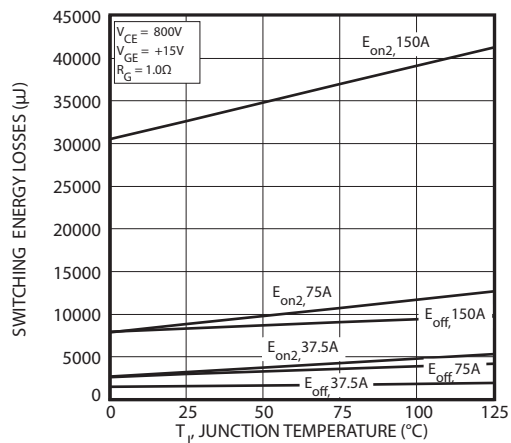


FIGURE 16, Switching Energy Losses vs Junction Temperature

TYPICAL PERFORMANCE CURVES

APT75GT120JRDQ3

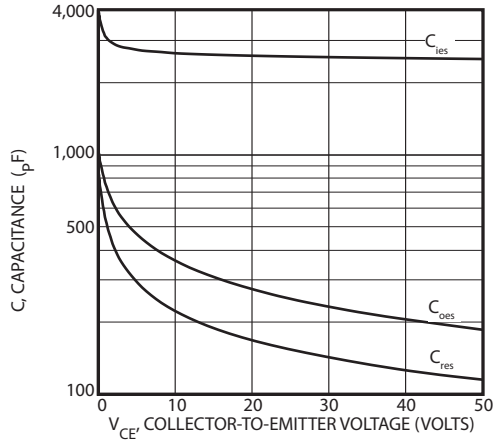


Figure 17, Capacitance vs Collector-To-Emitter Voltage

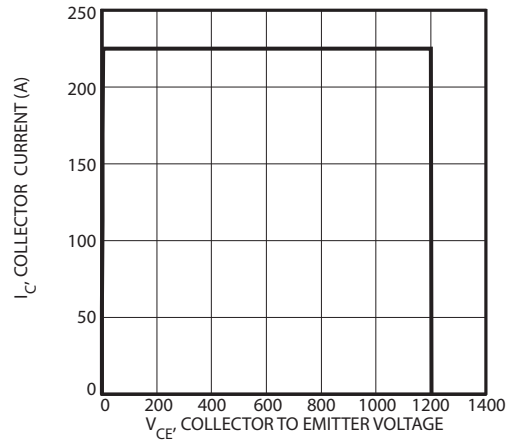


Figure 18, Minimum Switching Safe Operating Area

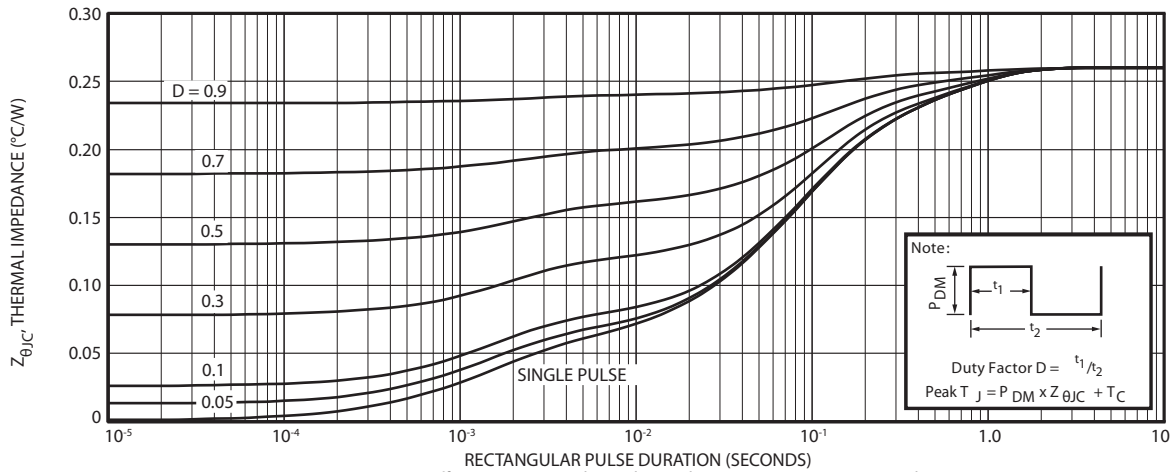


Figure 19, Maximum Effective Transient Thermal Impedance, Junction-To-Case vs Pulse Duration

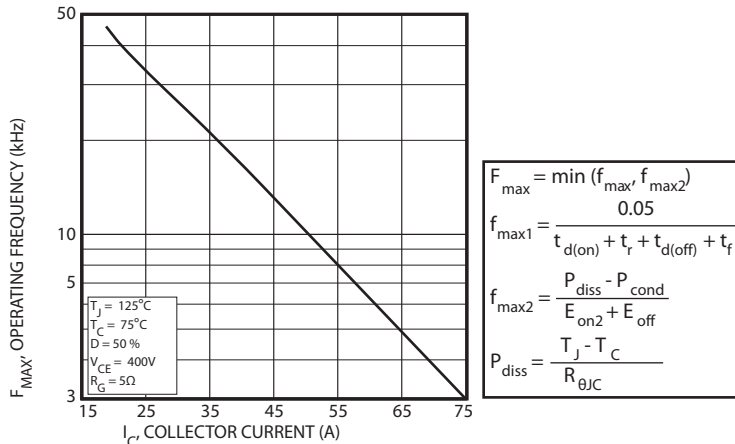


Figure 20, Operating Frequency vs Collector Current

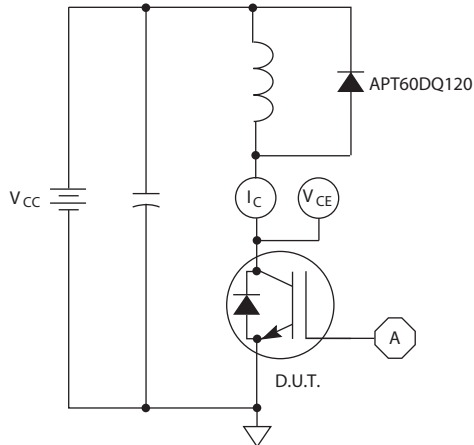


Figure 21, Inductive Switching Test Circuit

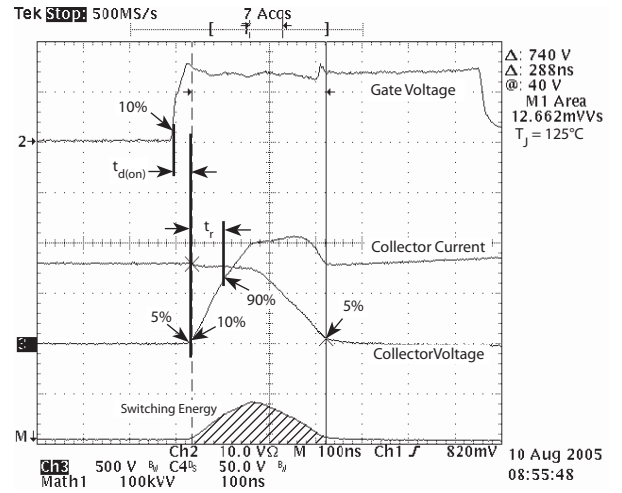


Figure 22, Turn-on Switching Waveforms and Definitions

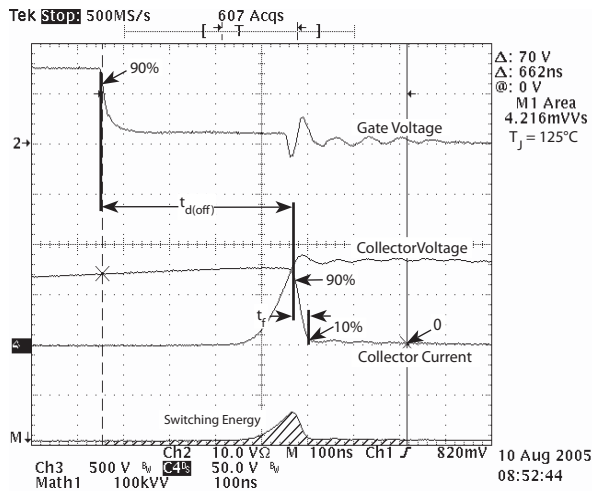


Figure 23, Turn-off Switching Waveforms and Definitions

# ULTRAFAST SOFT RECOVERY ANTI-PARALLEL DIODE

MAXIMUM RATINGS

All Ratings:  $T_C = 25^\circ\text{C}$  unless otherwise specified.

Symbol	Characteristic / Test Conditions	APT75GN120JRDQ3		UNIT
$I_F(AV)$	Maximum Average Forward Current ( $T_C = 85^\circ\text{C}$ , Duty Cycle = 0.5)	60		Amps
$I_F(RMS)$	RMS Forward Current (Square wave, 50% duty)	73		
$I_{FSM}$	Non-Repetitive Forward Surge Current ( $T_J = 45^\circ\text{C}$ , 8.3ms)	540		

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
$V_F$	Forward Voltage	$I_F = 75\text{A}$	2.8		Volts
		$I_F = 150\text{A}$	3.48		
		$I_F = 75\text{A}, T_J = 125^\circ\text{C}$	2.17		

DYNAMIC CHARACTERISTICS

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX-	UNIT
$t_{rr}$	Reverse Recovery Time	$I_F = 1\text{A}, di_F/dt = -100\text{A}/\mu\text{s}, V_R = 30\text{V}, T_J = 25^\circ\text{C}$	-	60		ns
$t_{rr}$	Reverse Recovery Time	$I_F = 60\text{A}, di_F/dt = -200\text{A}/\mu\text{s}, V_R = 800\text{V}, T_C = 25^\circ\text{C}$	-	265		
$Q_{rr}$	Reverse Recovery Charge		-	560		nC
$I_{RRM}$	Maximum Reverse Recovery Current		-	5	-	Amps
$t_{rr}$	Reverse Recovery Time	$I_F = 60\text{A}, di_F/dt = -200\text{A}/\mu\text{s}, V_R = 800\text{V}, T_C = 125^\circ\text{C}$	-	350		ns
$Q_{rr}$	Reverse Recovery Charge		-	2890		nC
$I_{RRM}$	Maximum Reverse Recovery Current		-	13	-	Amps
$t_{rr}$	Reverse Recovery Time	$I_F = 60\text{A}, di_F/dt = -1000\text{A}/\mu\text{s}, V_R = 800\text{V}, T_C = 125^\circ\text{C}$	-	150		ns
$Q_{rr}$	Reverse Recovery Charge		-	4720	-	nC
$I_{RRM}$	Maximum Reverse Recovery Current		-	40		Amps

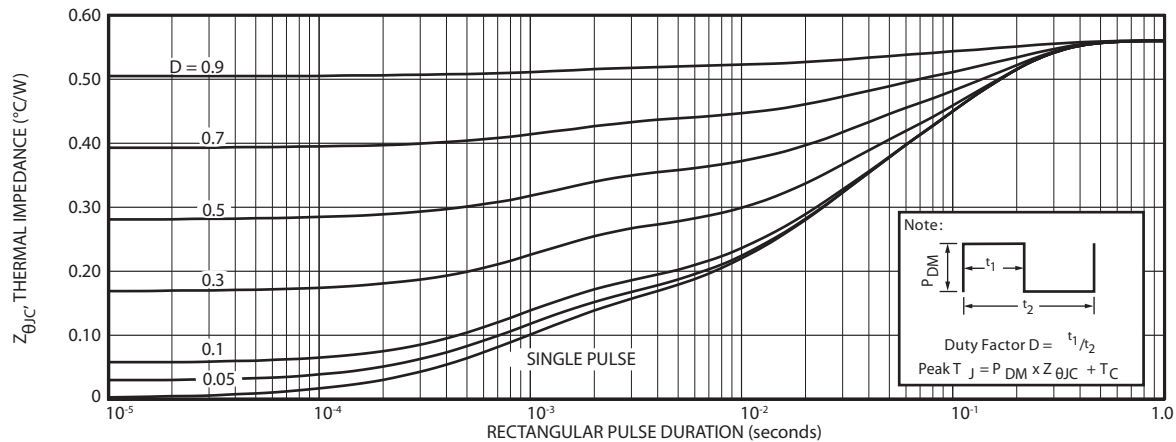


FIGURE 24. MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs. PULSE DURATION

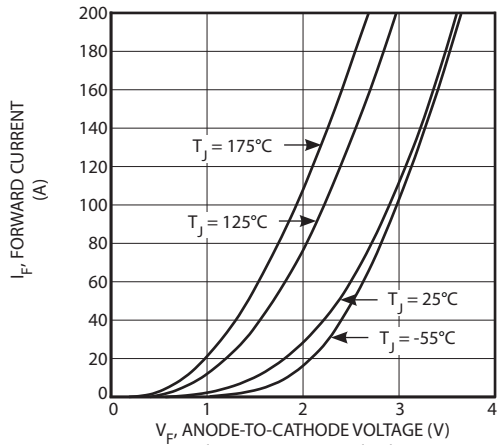


Figure 25. Forward Current vs. Forward Voltage

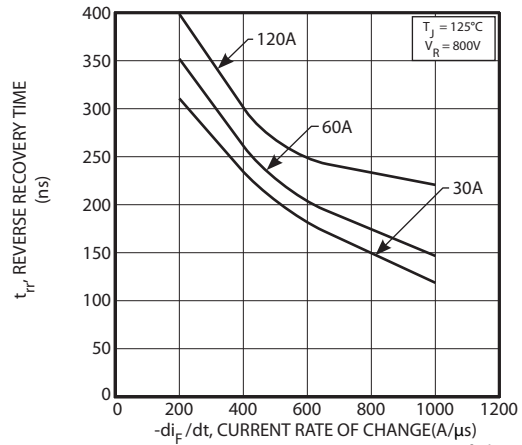


Figure 26. Reverse Recovery Time vs. Current Rate of Change

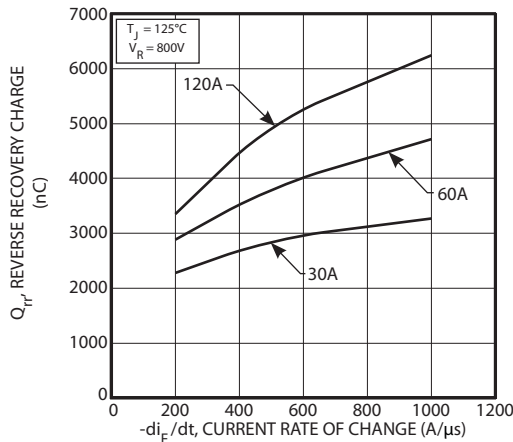


Figure 27. Reverse Recovery Charge vs. Current Rate of Change

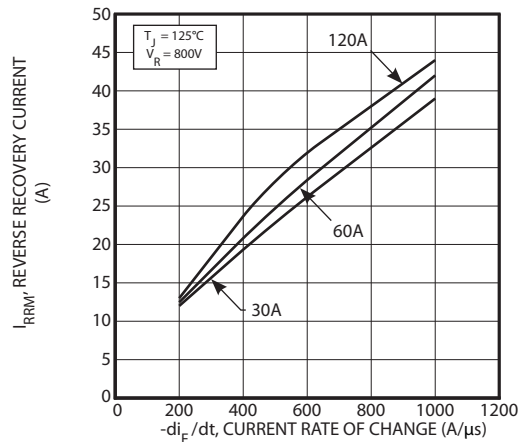


Figure 28. Reverse Recovery Current vs. Current Rate of Change

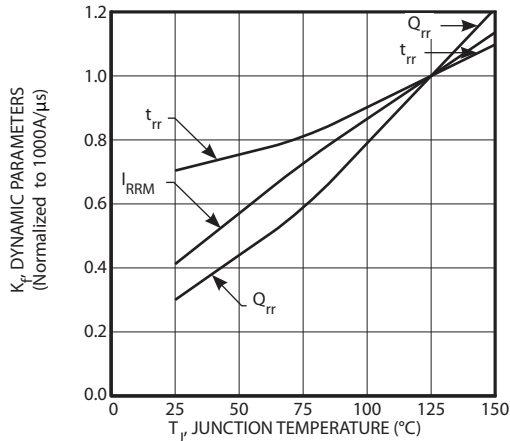


Figure 29. Dynamic Parameters vs. Junction Temperature

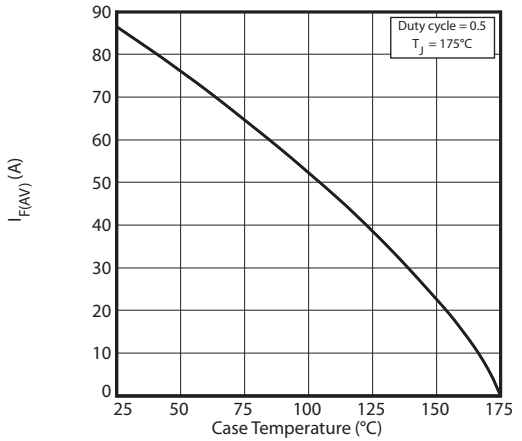


Figure 30. Maximum Average Forward Current vs. Case Temperature

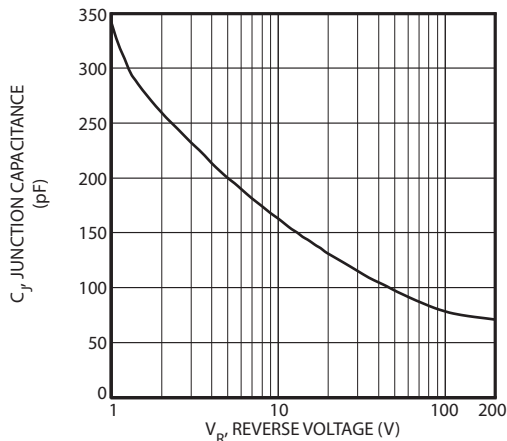


Figure 31. Junction Capacitance vs. Reverse Voltage



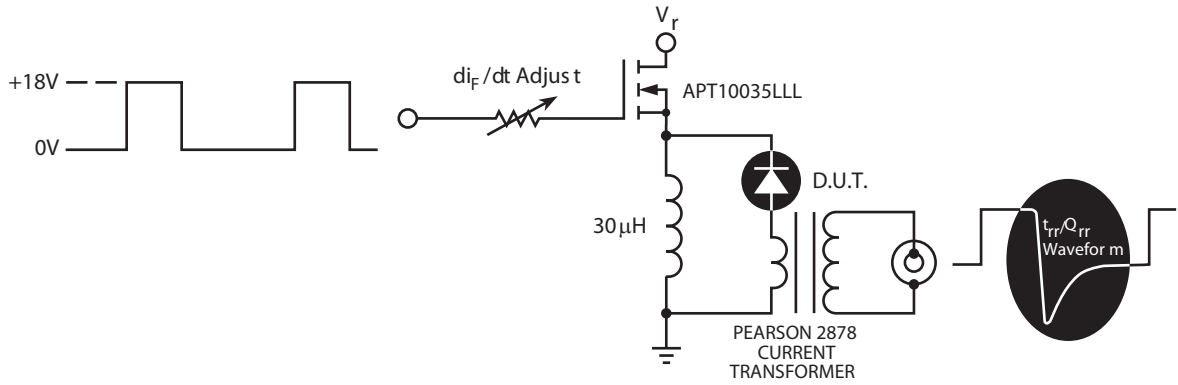


Figure 32. Diode Test Circuit

- 1  $I_F$  - Forward Conduction Current
- 2  $di_F/dt$  - Rate of Diode Current Change Through Zero Crossing.
- 3  $I_{RRM}$  - Maximum Reverse Recovery Current
- 4  $t_{rr}$  - Reverse Recovery Time, measured from zero crossing where the diode current goes from positive to negative, to the point at which the straight line through  $I_{RRM}$  and  $0.25 I_{RRM}$  passes through zero.
- 5  $Q_{rr}$  - Area Under the Curve Defined by  $I_{RRM}$  and  $t_{rr}$ .

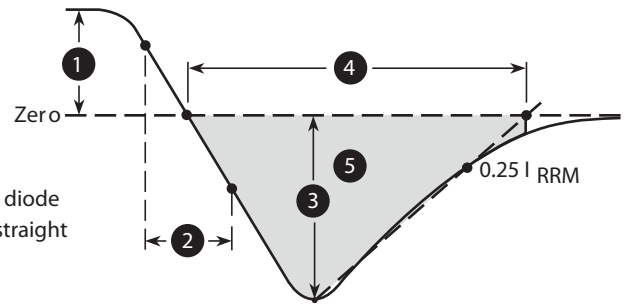
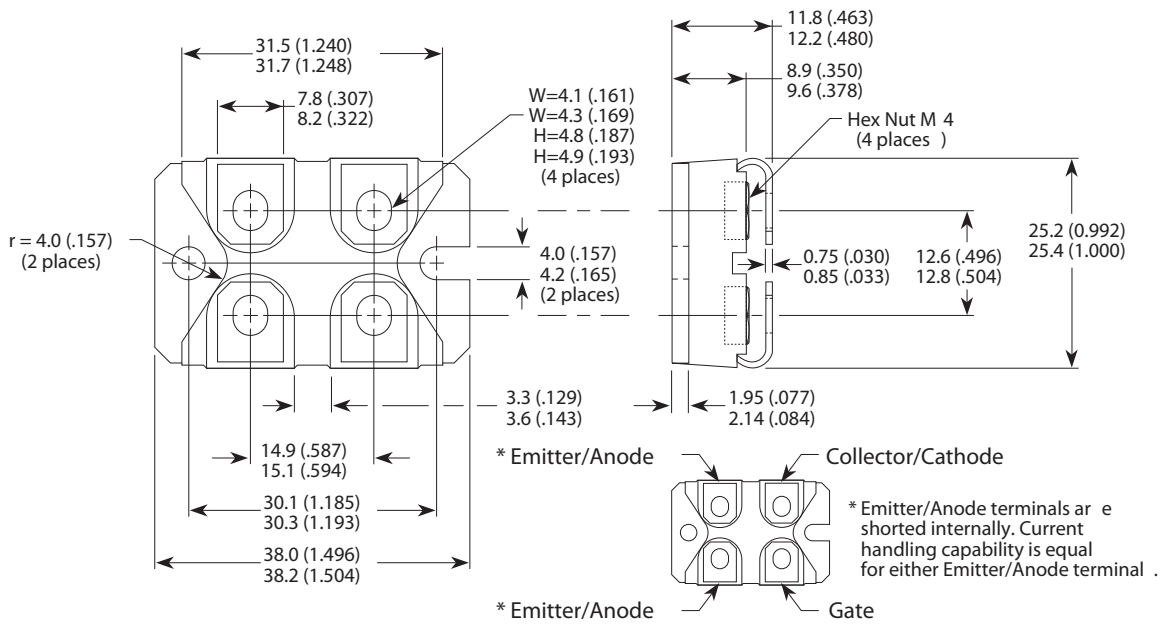


Figure 33. Diode Reverse Recovery Waveform and Definitions

SOT-227 (ISOTOP®) Package Outline



Dimensions in Millimeters and (Inches)